# **GSDE1** AF Series

# **Fast Recovery Diode**

# **Product Description**

Reverse Voltage 200V to 600V. Forward Current 1.0A

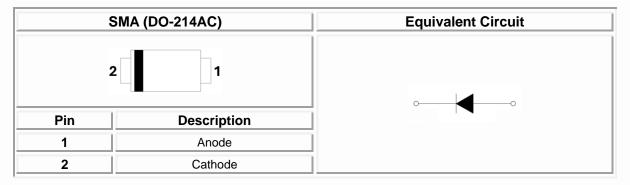
## **Features**

- 35ns Max Reverse Recovery Time
- RoHS Compliant and Halogen Free

# **Mechanical Data**

- SMA (DO-214AC) Package
- Polarity: Color Band denotes Cathode End

# **Package and Pin Assignment**



# **Ordering and Marking Information**

Ordering Information			
Part Number	V <sub>RRM</sub>	Marking Code	Quantity/Reel
GSDE1DAF	200	ES1D	5000 PCS
GSDE1GAF	400	ES1G	5000 PCS
GSDE1JAF	600	ES1J	5000 PCS

**★** GSDE1DAF can be selected if required V<sub>RRM</sub> of 50V, 100V and 150V.

# GSDE1 1 A F

- **Product Code:**GSDE1
- Voltage Code:
   is D. G or J stands for Maximum repetitive peak

reverse voltage.

Package Code:A for SMA (DO-214AC)Package

- Green Level:

**F** for RoHS Compliant and Halogen Free



# **Marking Information**

ES1 1

- Product Code:

ES1

- Voltage Code:

1 is D. G or J stands for Maximum repetitive peak reverse voltage.

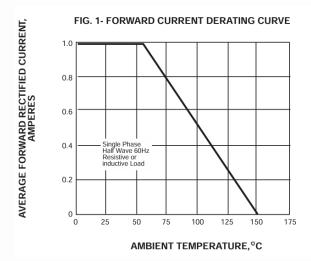
# Electrical Characteristics (Ratings at 25°C Ambient Temperature Unless Otherwise Specified.)

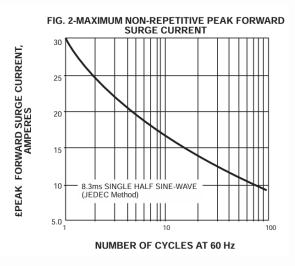
Symbol	Conditions		E1D	E1G	E1J	Unit
V <sub>RRM</sub>	Maximum Recurrent Peak Reverse Voltage		200	400	600	V
V <sub>RMS</sub>	Maximum RMS Voltage		140	280	420	V
V <sub>DC</sub>	Maximum DC Blocking Voltage		200	400	600	V
I <sub>F(AV)</sub>	Maximum Average Forward Rectified Current		1			Α
I <sub>FSM</sub>	Peak Forward Surge Current (8.3ms Single Half Sinewave)		30			A
VF	Maximum Fo Voltage at 1.0		0.95	1.25	1.7	V
	Maximum Reverse Leakage Current at rated V <sub>R</sub>	T <sub>A</sub> = 25°C	5			μΑ
I <sub>R</sub>		T <sub>A</sub> = 100°C		50		μΑ
trr	Maximum reverse recovery time (1)			35		
Сл	Typical Junction Capacitance (2)		15			pF
$R_{ heta}$ JA	Typical Thermal Resistance <sup>(3)</sup>		60			°C/W
TJ	Operating Junction Temperature Range		-55 to +150			°C
T <sub>STG</sub>	Storage Temperature Range			-55 to +150		

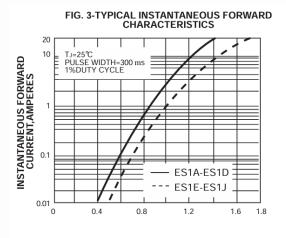
- 1. Measured with  $I_F=0.5A$ ,  $I_R=1A$ , Irr=0.25A.
- Measured at 1MHz and applied reverse voltage of 4.0V<sub>DC</sub>
   Mounted with 0.2 x 0.2" (5.0 x 5.0mm) Copper Pad Areas

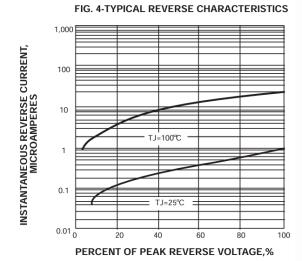


# Typical Characteristics (Ratings at 25°C Ambient Temperature Unless Otherwise Specified.)

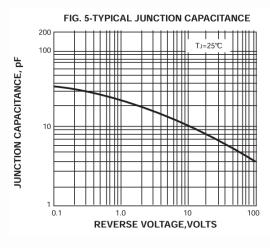


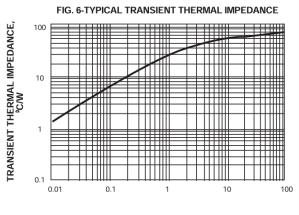












t.,PULSE DURATION,sec.

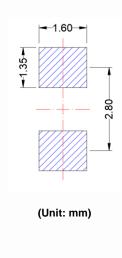


# **SMA (DO-214AC)**

# **Package Dimension**

# BACKSIDE VIEW

# **Recommended Land Pattern**



	Dimensions			
Comple at	Millimeters		Inches	
Symbol	Min	Max	Min	Max
Α	0.80	1.10	0.031	0.043
b	0.50	1.20	0.020	0.047
D	1.50	1.90	0.059	0.075
E	3.30	3.80	0.130	0.150
E1	2.45	2.75	0.096	0.108
С	0.05	0.20	0.002	0.008
L	0.70	0.90	0.028	0.035

# NOTE:

- 1. Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.
- 2. Terminals are partially uncovered on the bottom of package body



# **NOTICE**

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